

【ABSTRACT】

The present invention relates to a gallium nitride-based compound semiconductor device and a method of manufacturing the same. According to the present invention, there is provided a gallium nitride-based III-V group compound semiconductor device comprising a gallium nitride-based semiconductor layer and an ohmic electrode layer formed on the gallium nitride-based semiconductor layer. The ohmic electrode layer comprises a contact metal layer, a reflective metal layer, and a diffusion barrier layer.